

JST136C-800D 4A TRIAC

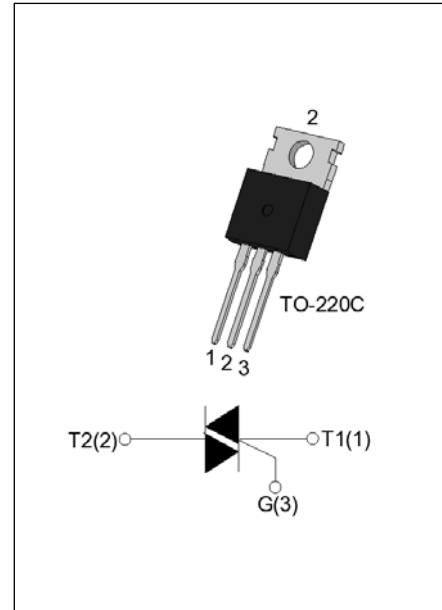
Rev.A.1.0

DESCRIPTION:

The JST136C-800D triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	5/5/5/10	mA


ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)		V_{RRM}	800	V
RMS on-state current ($T_c \leq 110^{\circ}C$)		$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)		I_{TSM}	35	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)			38.5	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)		I^2t	6.1	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	I - II -III	di/dt	50	$A/\mu s$
	IV		40	
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)		I_{GM}	2	A
Average gate power dissipation ($T_j=125^{\circ}C$)		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W
Peak pulse voltage ($T_j=25^{\circ}C$; non-repetitive,off-state;FIG.7)		V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX.	5	mA
		IV		10	
V_{GT}		ALL	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	15	mA
		II - IV		25	
I_H	$I_T=100\text{mA}$		MAX.	15	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=110^{\circ}\text{C}$		MIN.	100	$\text{V}/\mu\text{s}$
$(dV/dt)_c$	$(dI/dt)_c=1.8\text{A/ms}$, $T_j=110^{\circ}\text{C}$		MIN.	2.5	$\text{V}/\mu\text{s}$
t_{on}	$I_G=20\text{mA } I_A=200\text{mA } I_R=20\text{mA}$		TYP.	1	μs
t_{off}	$T_j=25^{\circ}\text{C}$			12	

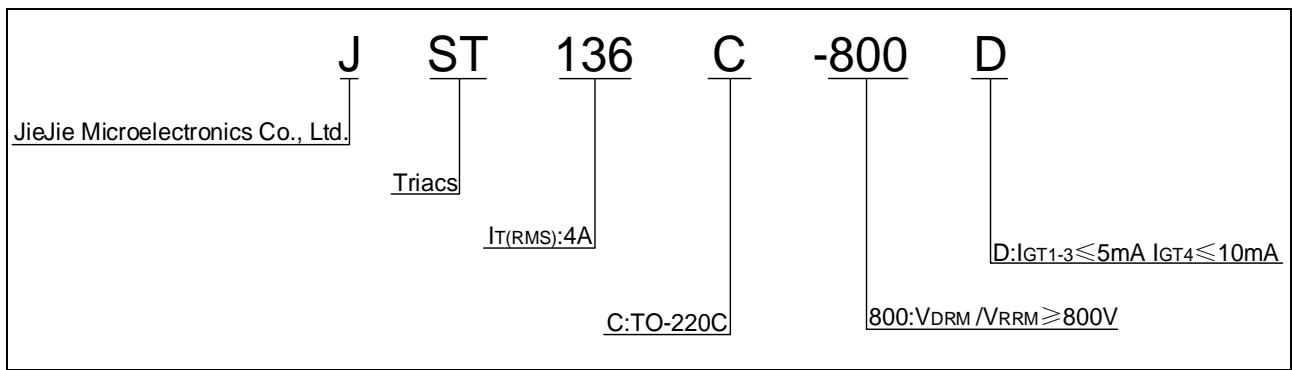
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5\text{A } t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.7	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.94	V
R_D	Dynamic resistance	$T_j=125^{\circ}\text{C}$	124	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.3	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

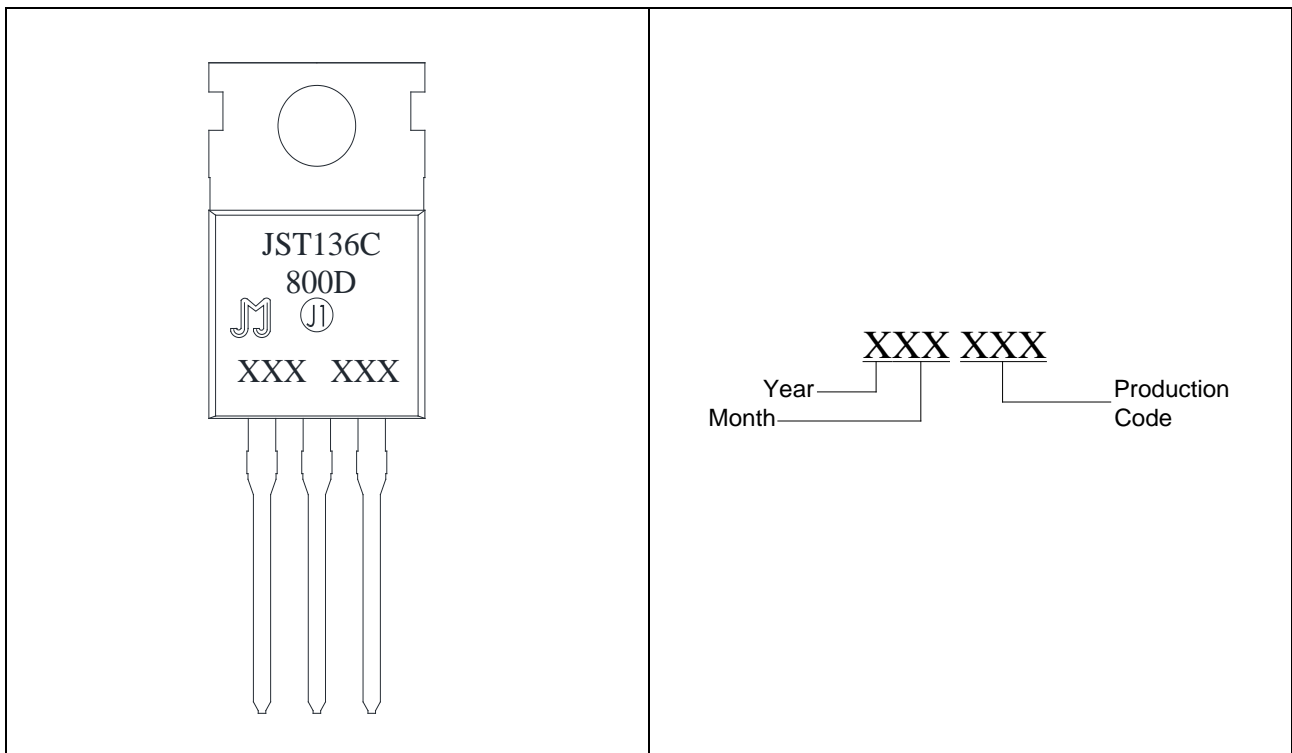


FIG.1 Maximum power dissipation versus RMS on-state current

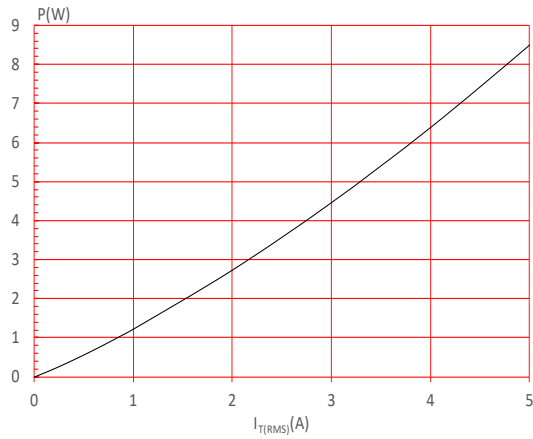


FIG.2: RMS on-state current versus case temperature

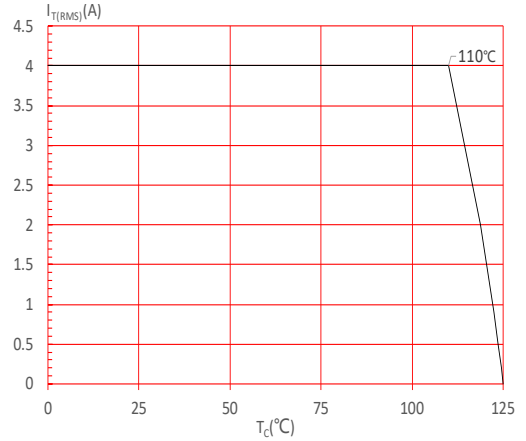


FIG.3: Surge peak on-state current versus number of cycles

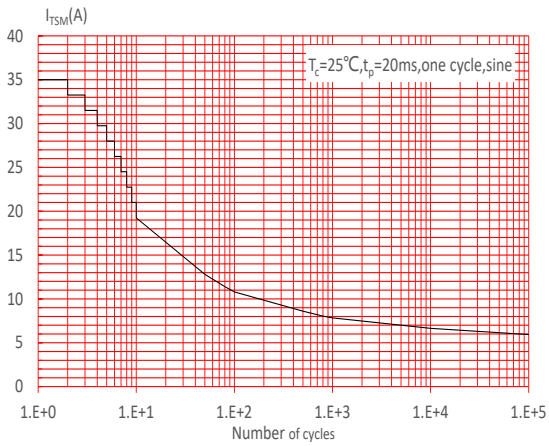


FIG.4: On-state characteristics

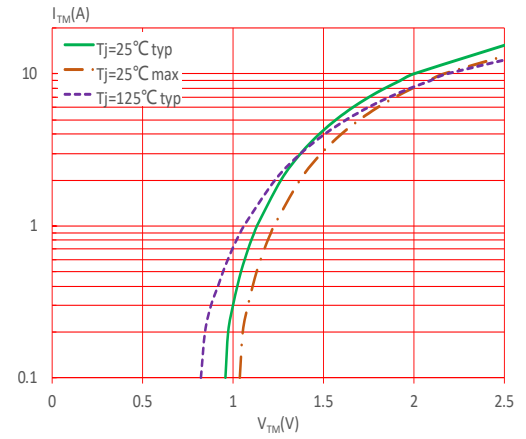


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $di/dt < 50\text{A}/\mu\text{s}$; IV: $di/dt < 40\text{A}/\mu\text{s}$)

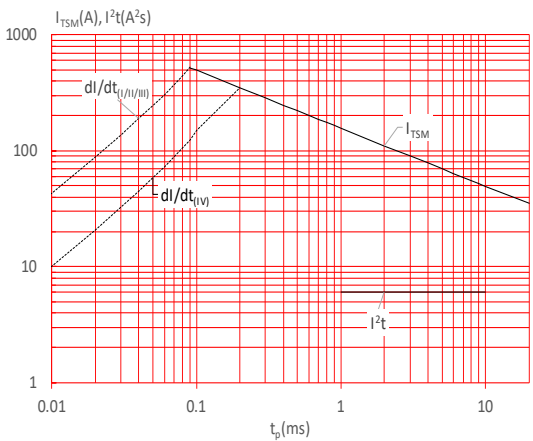


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

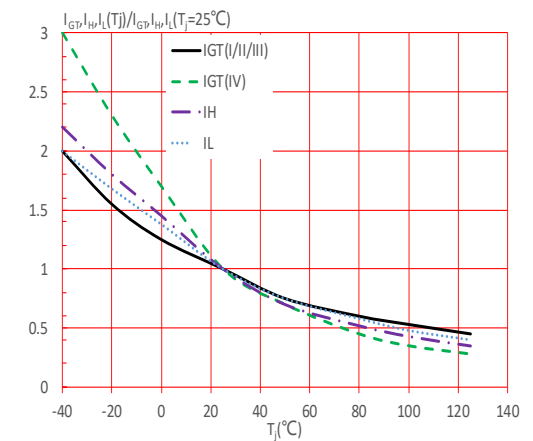
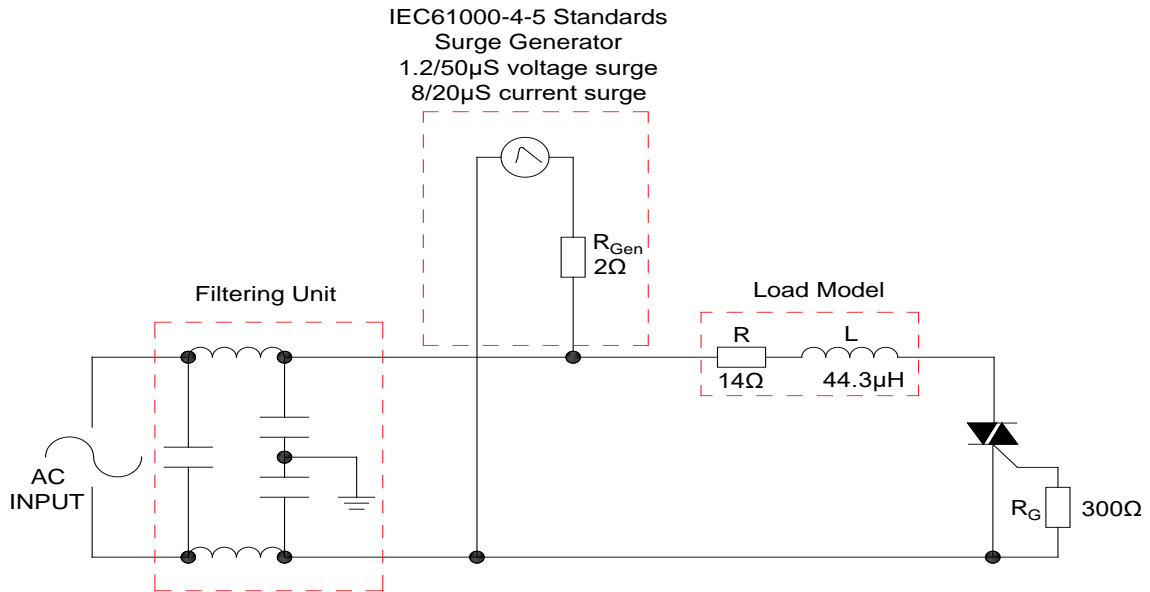


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II-III	IV			
JST136C-800D	800	5	10	TO-220C	50	Tube

Document Revision History

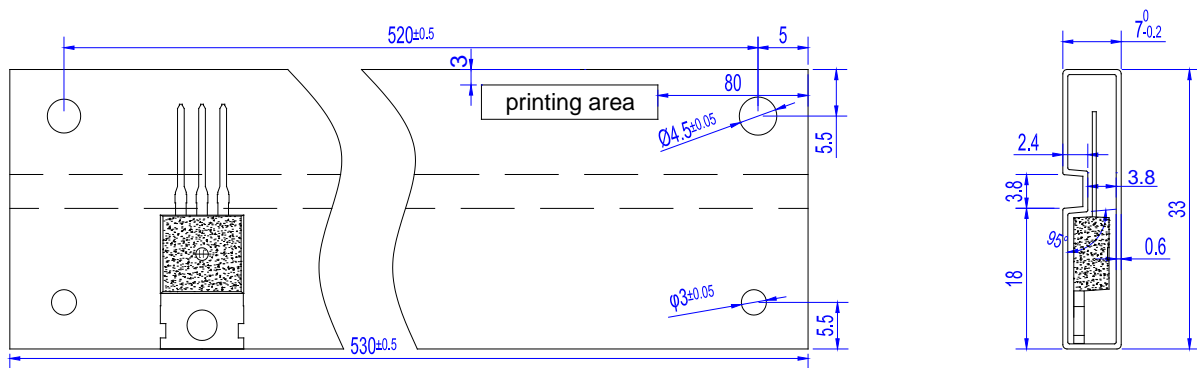
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

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